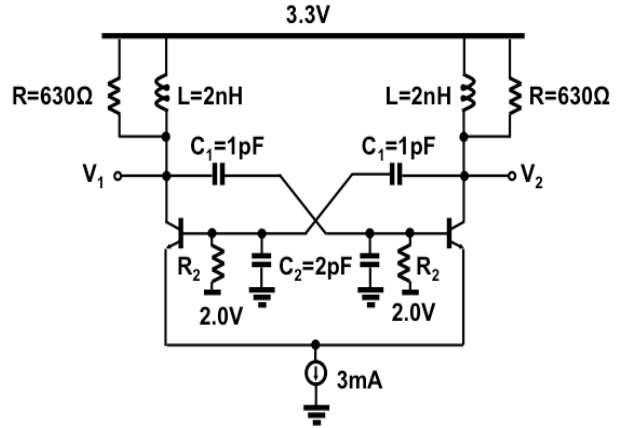


Tutorial T8

T8.1 Let us consider the oscillator in the figure.
Assume infinite β and $V_{BE,on} = 0.7V$, $V_{BC,sat} = 0.5V$ for the BJTs.

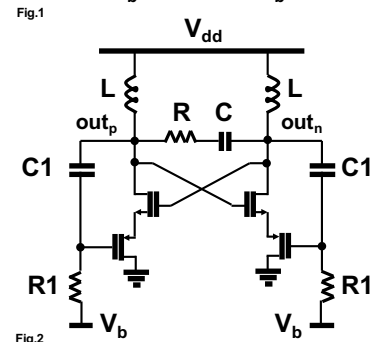
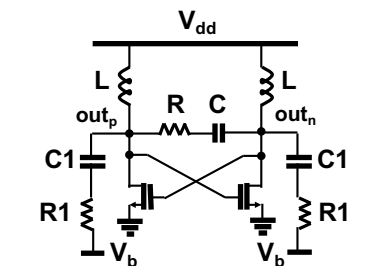
- Derive the circuit bias point.
- Neglecting R_2 and r_{π} of the BJTs, evaluate both oscillation frequency and start-up margin.
- Assuming full-switching of the differential pair, evaluate the oscillation amplitude and provide a plot of base and collector voltages of the BJTs over one period. Analyze the operating regions of the BJTs during the oscillation period and discuss the purpose of C_1 and C_2 .
- How is the tank resistance modified by a finite value of R_2 ? Size R_2 in order to worsen the quality factor of the resonant network by maximum 10%.



[Sol. a) $I_C = 1.5mA$, $V_E = 1.3V$, $V_B = 2.0V$, $V_C = 3.3V$, $g_m = 60mS$; b) $f_0 = 4.36$ GHz, $g_m R C_1 / (C_1 + C_2) = 12.6 > 1$; c) $A = 2.4V$; the base-collector voltage, V_{BC} , ranges between $-2.9V$ and $+0.3V$; the BJTs go from cut-off to forward active region. C_1 and C_2 help reduce the oscillation amplitude of the base voltage, allowing for a higher oscillation amplitude before incurring in saturation of the BJTs; d) $R_2 = 630\Omega$.]

T8.2 Let $V_b = 0.15V$, $L = 1nH$, $R = 10\Omega$, $C = 250fF$, $C1 = 1pF$, $R1 = 1k\Omega$, $\mu_{C_{ox}}(W/L) = 120mA/V^2$ (nMOS), $\mu_{C_{ox}}(W/L) = 56mA/V^2$ (pMOS) and $V_t = 0.45V$ for all transistors.

- With reference to the circuit in Fig. 1 (let $V_{dd} = 0.55V$), after deriving the bias current flowing into the FETs, calculate the frequency of oscillation and the gain margin for the oscillation start-up (i.e. the loop gain at the oscillation frequency).
- With reference to the circuit in Fig. 2 (let $V_{dd} = 1.5V$), after deriving the bias current flowing into the FETs, calculate the frequency of oscillation and the gain margin for the oscillation startup.



[Sol. a) $I = 600$ uA, $f_0 = 7.114GHz$, $|LG(j\omega_0)| = 3.4$; b) $I = 2mA$, $f_0 = 7.114GHz$, $|LG(j\omega_0)| = 5$]